

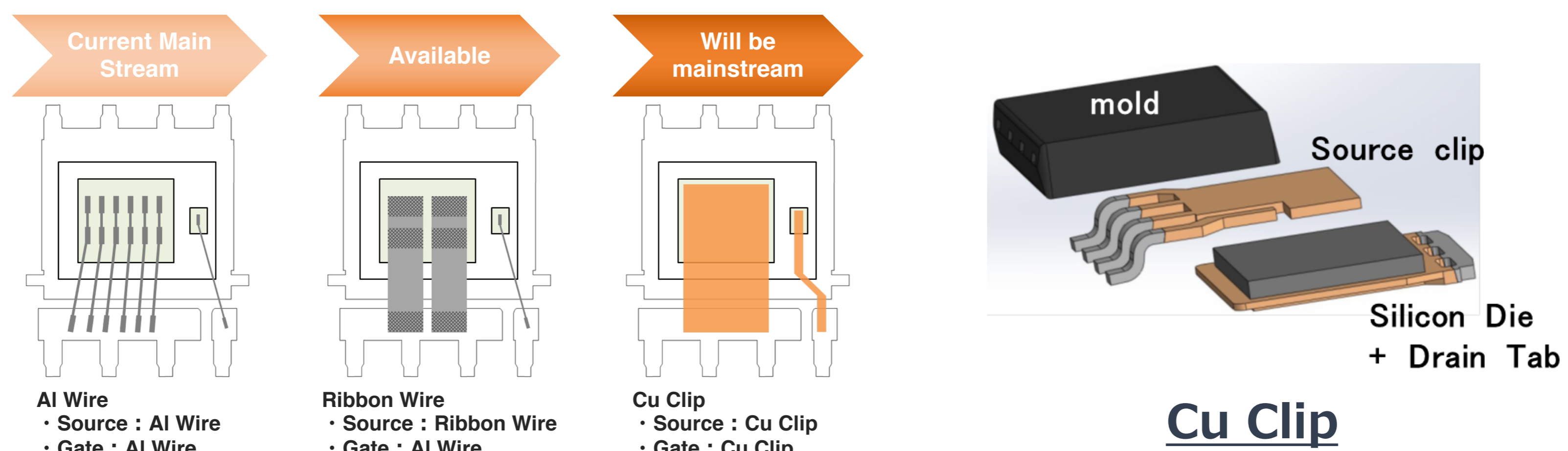
40V~120V MOSFET EETMOS Series ^{※1} Extremely Efficient Trench gate MOSFET

Shindengen has developed smaller high current LF package and also TO-263-7 for on-board-vehicle adopting new higher heat dissipation by, achieving lower Rds(on) and Lower Qg(Pf) compared with current products.

New Structure Package Adoption ! <LF/TO-263-7>

Due to Cu-Clip structure, Low R(ds)on, small size and Thinner Large Current are achieved !

- Tj = 175°C
- AEC-Q101 Qualified
- LF : 5×6mm (Footprint is compatible with SOP8, HSON-Family)
- Due to Gull-Wing on one side of lead-wire, stress of the substrate is effectively reduced
- Achieved higher reliability mounting due to plating process on the edge of Lead-wire



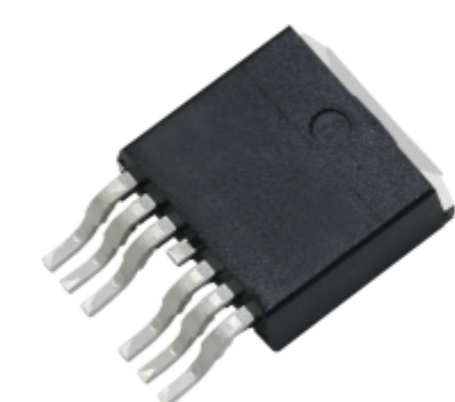
[LF Spec example]

Part Name	V _{DS} (min) [V]	I _D (min) [A]	V _{TH} (typ) [V]	Ron [mΩ]		Ciss VDS=25V (typ) [pF]	Coss VDS=25V (typ) [pF]	Crss VDS=25V (typ) [pF]	Based on AEC-Q101
				V _{GS} =10V					
				(typ)	(max)				
P140LF4QNK	40	140	3.0	1.2	1.4	5740	830	500	○
P98LF6QNK	60	98	3.0	2.5	3.1	5780	570	340	○



[TO-263-7 Spec example]

Part Name	VDS (min) [V]	ID (max) [A]	VTH (typ) [V]	Ron[mΩ]		Ciss VDS=2 5V (typ) [pF]	Coss VDS=2 5V (typ) [pF]	Crss VDS=2 5V (typ) [pF]	Based on AEC-Q101
				VGS=10V					
				(typ)	(max)				
P240FZ4QNK	40	240	3.0	1.01	1.27	8410	1210	730	Planned
P170FZ6QNK	60	170	3.0	1.94	2.5	8470	840	490	Planned



- SOP (LF 2018) : DEC 2018 ^{※2}
- SOP (TO-263-7): Apr 2019 ^{※2}

- ※1 EETMOS is our trademark registration.
- ※2 The release timing might be changed due to development progress.